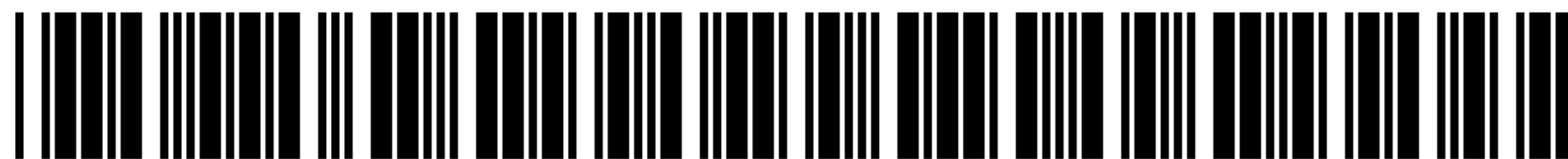


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Integratable Programmable Capacitive Device

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(54) **INTEGRATABLE PROGRAMMABLE
CAPACITIVE DEVICE**

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See application file for complete search history.

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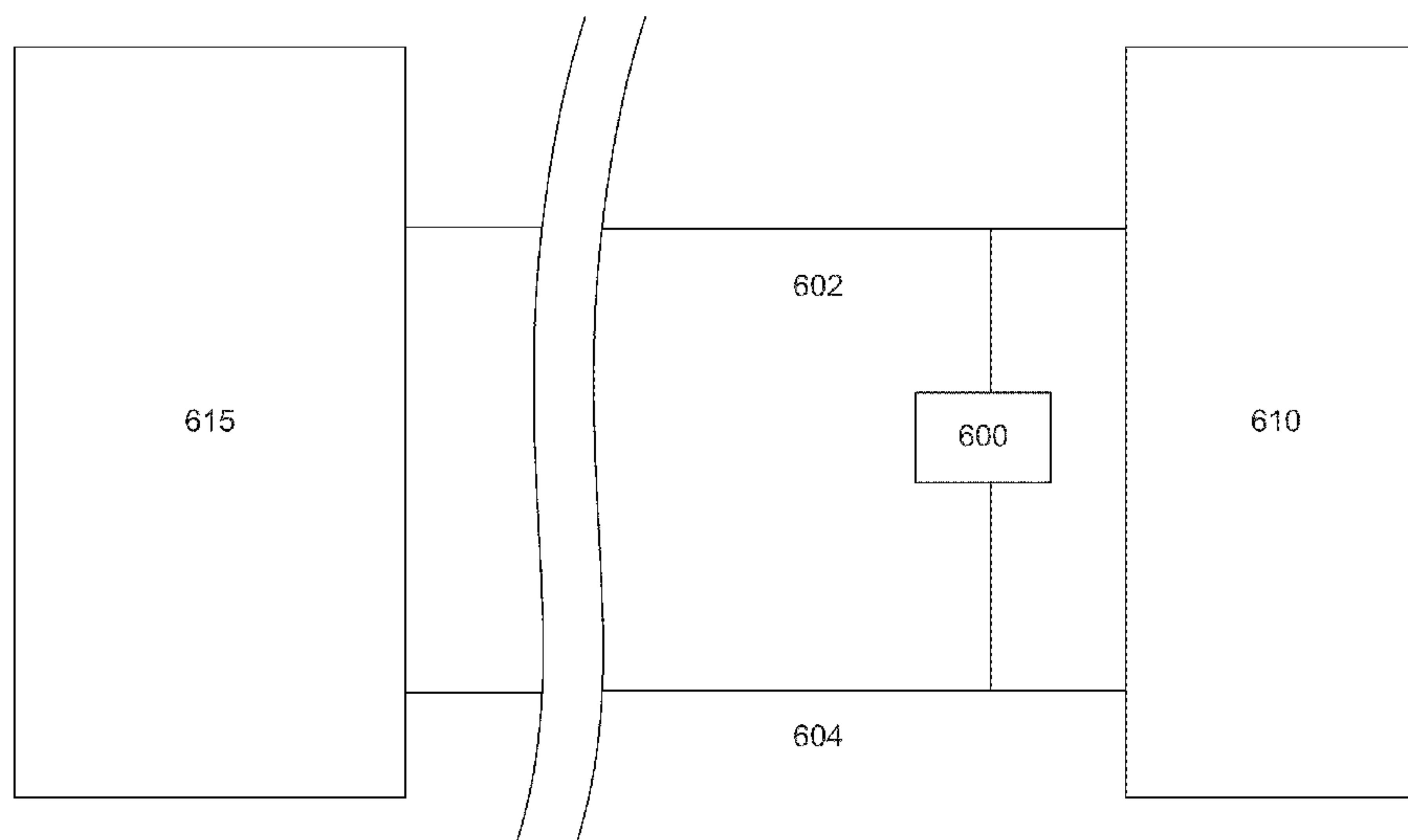
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(57) **ABSTRACT**

A circuit with a capacitive device is disclosed. The circuit may comprise a capacitive device connected between a first conductor and a second conductor. The capacitive device may comprise a first electrode connected to the first conductor and a second electrode being connected to the second conductor. A chalcogenide layer may be connected to the first electrode and to a metal chalcogenide layer.

20 Claims, 6 Drawing Sheets



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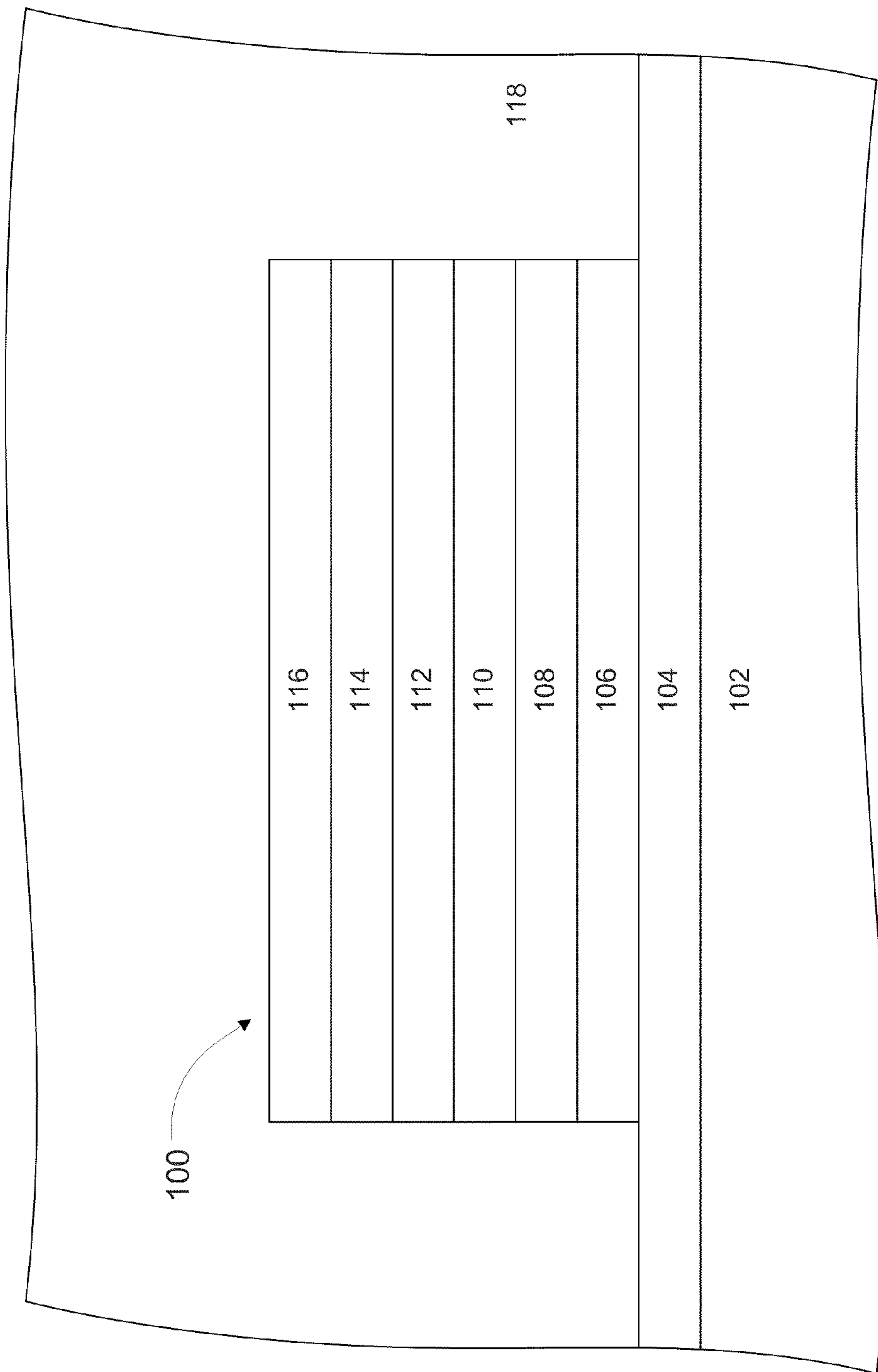


FIG. 1

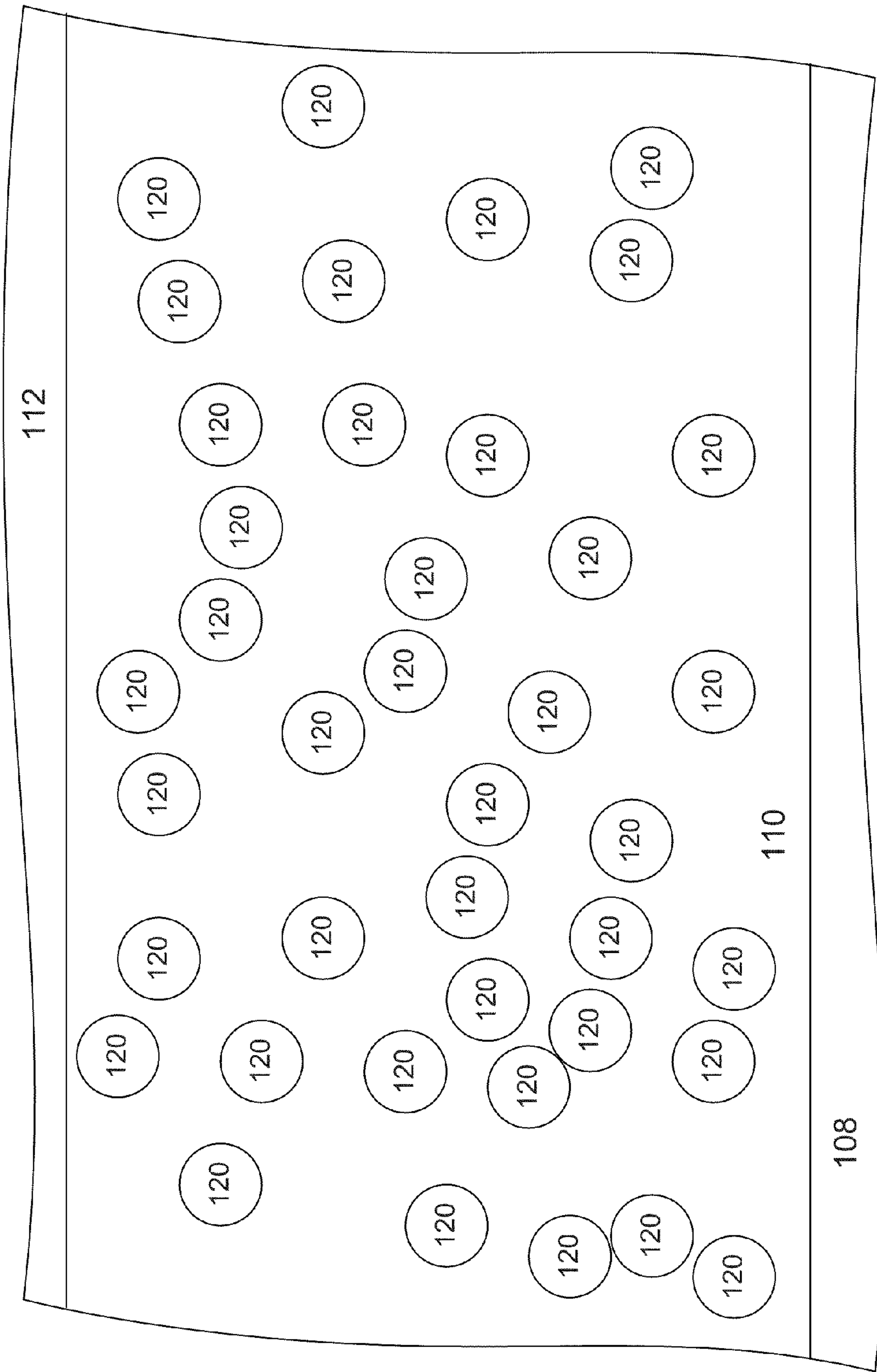


FIG. 2

IV Curve:

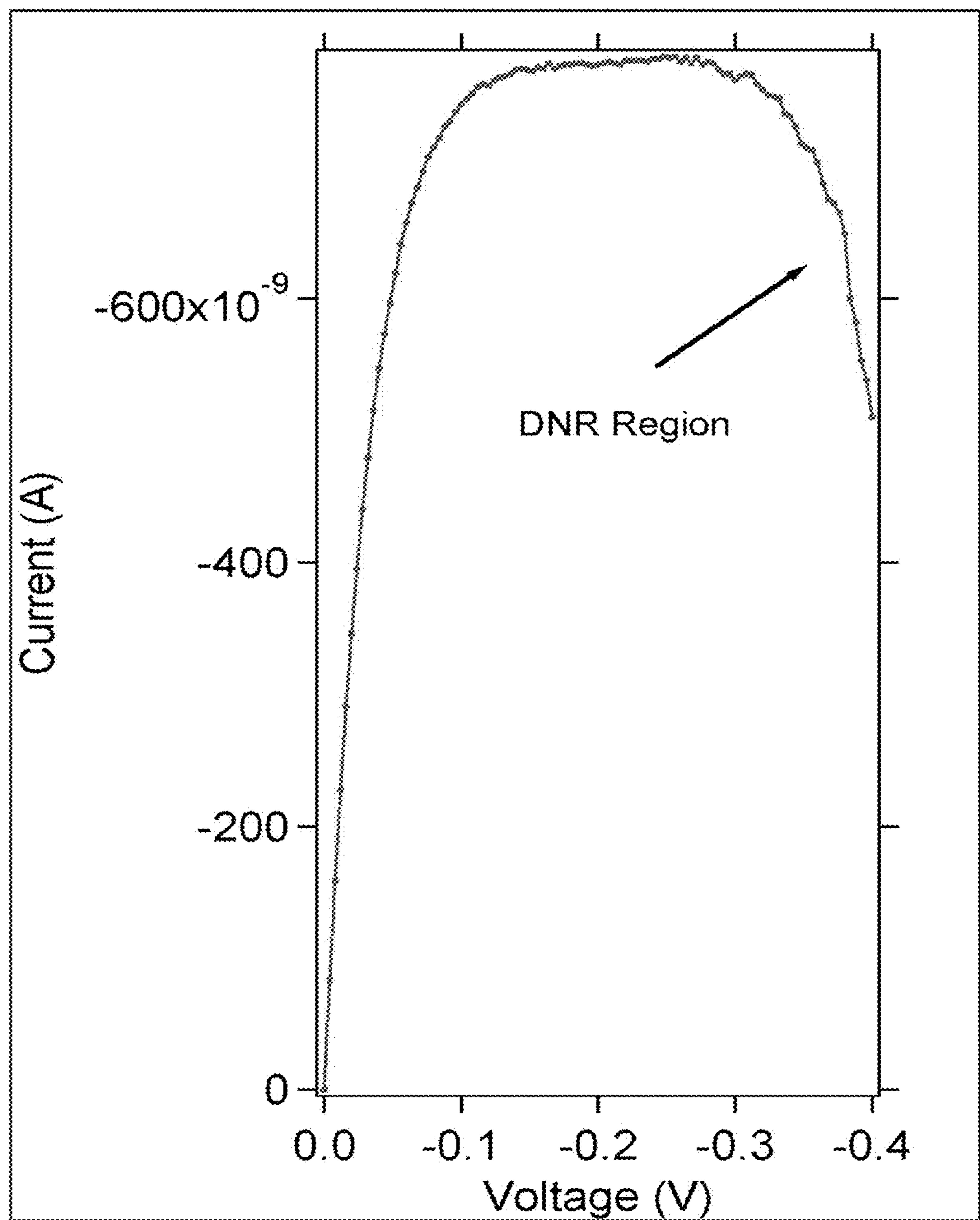


FIG. 3

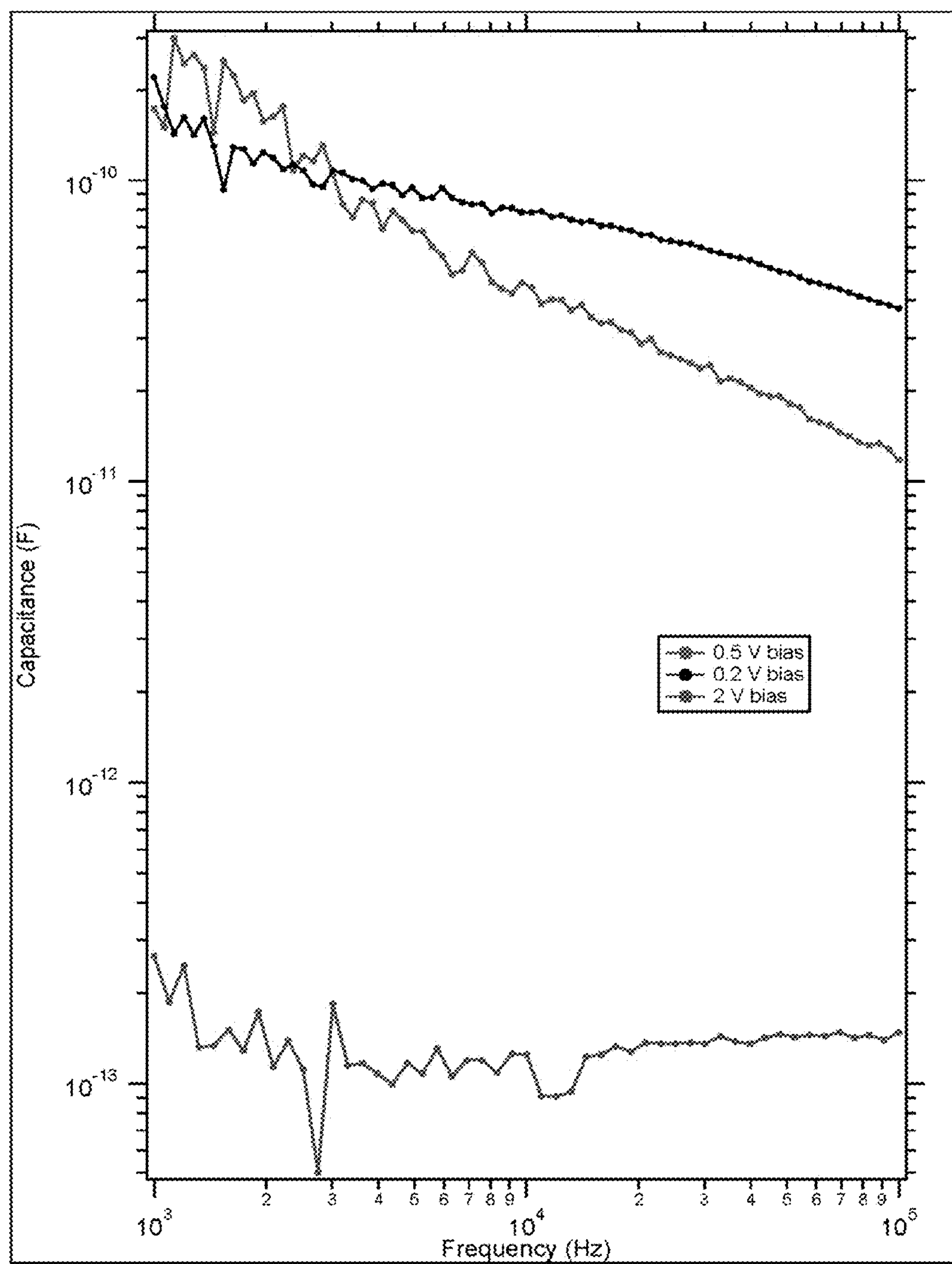


FIG. 4

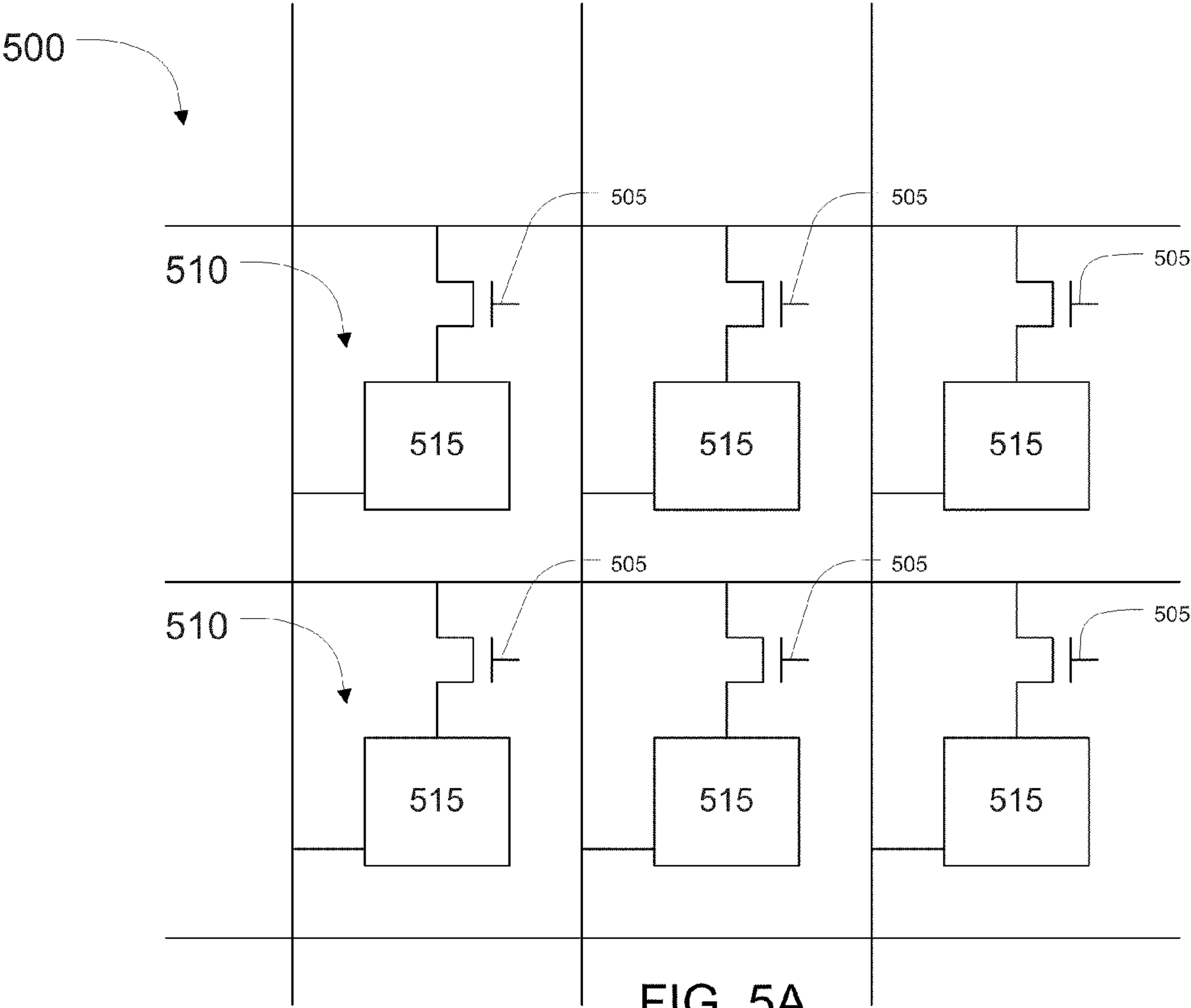


FIG. 5A

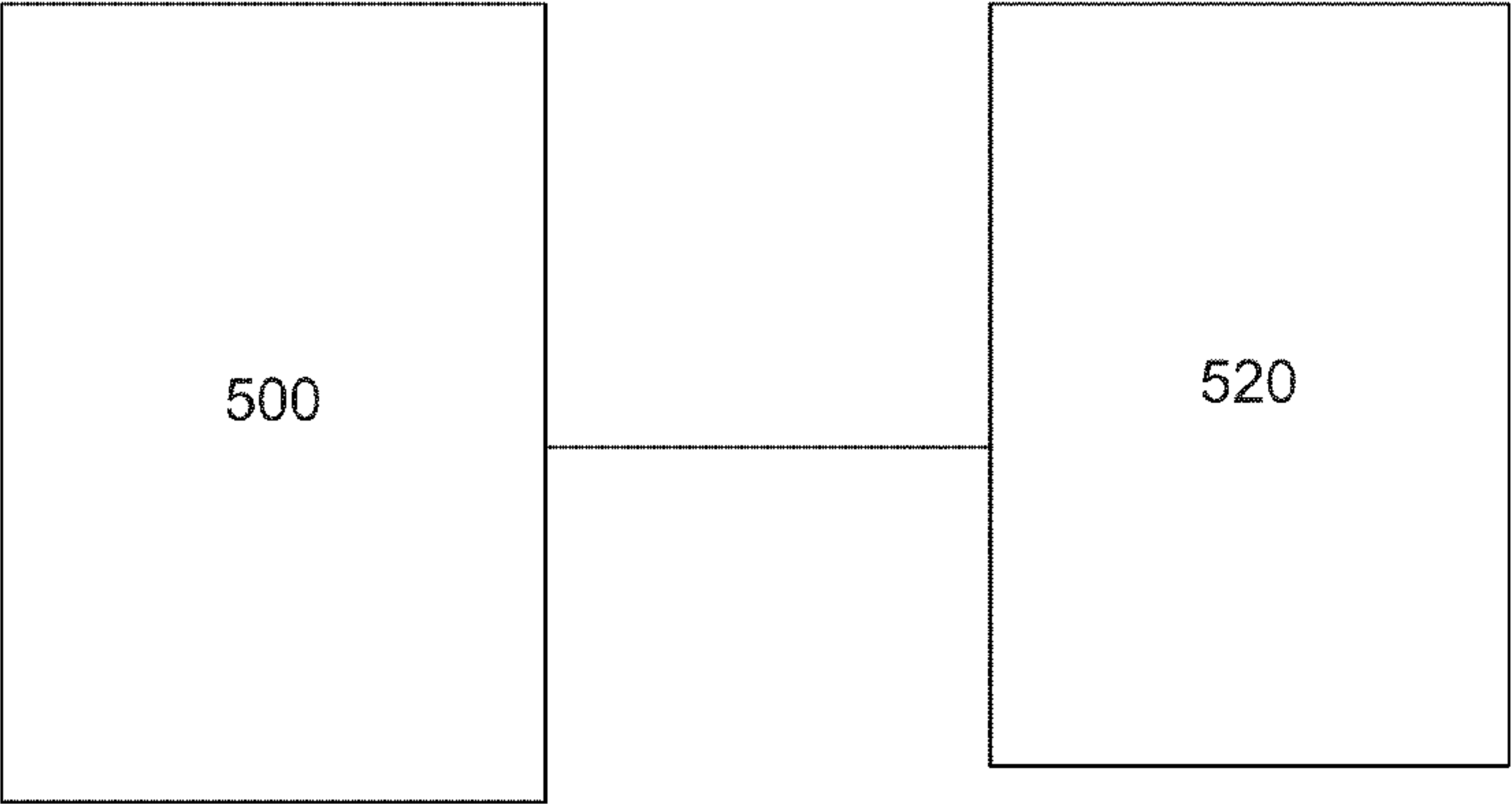


FIG. 5B

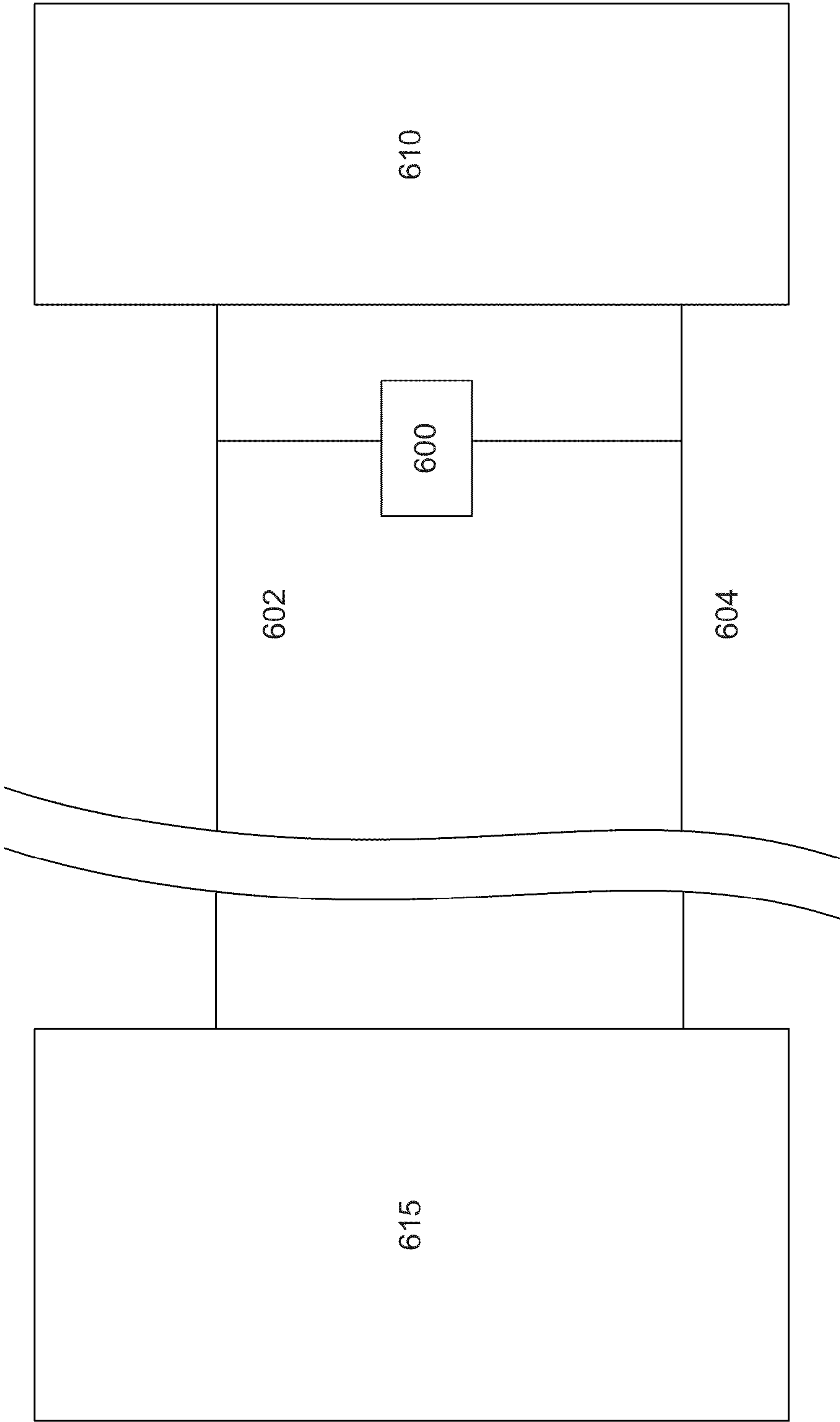


FIG. 6

INTEGRATABLE PROGRAMMABLE CAPACITIVE DEVICE

BACKGROUND

The present application relates generally to capacitive devices that may be used in an electric circuit. More specifically, the disclosure relates to a device comprising chalcogenide material and uses for the chalcogenide based device within a circuit, such as, for example, a Dynamic Random Access Memory (DRAM) circuit and/or a power related circuit.

Devices that comprise chalcogenide materials have previously been used in electric circuits. The tunnel diode exhibits a number of interesting attributes, such as fast switching and differential negative resistance (“DNR”) (sometimes alternatively referred to as negative differential resistance or NDR). The tunnel diodes typically employ a quantum mechanical effect called the tunnel effect, which may be characterized by a non-ohmic behavior, such as by a non-linear current-voltage (I-V) curve.

Generally, ohmic devices, as opposed to non-ohmic devices, can be described by Ohm’s law, $V=IR$, which states that current through a device is directly proportional to the voltage across the device. Thus, regarding an ohmic device, a larger current is seen through the ohmic device when a larger voltage is applied across the device. Typically, the I-V curve of an ohmic device shows a curve starting at the zero points of both voltage and current, with the curve increasing from the bottom left toward the top right of the graph, and showing consistently increasing current with increasing voltage. By contrast, the I-V curve of a device exhibiting DNR will show a rise from the zero points of voltage and current, to a peak, then a decrease from that peak, showing a decrease in current as the voltage continues to increase.

U.S. Pat. No. 7,015,494 (“the ’494 patent”), to Campbell, describes an assembly comprising a chalcogenide material. The assembly demonstrates DNR and may be used for a device such as a tunnel diode. The ’494 patent is incorporated herein, in its entirety, by reference.

Generally, DRAM circuits use a capacitive memory element to store charge, which may be used to indicate a binary value. Large banks of capacitive charge containers are used in modern DRAM circuits and are closely spaced when fabricated. The containers are packed together to minimize the footprint of the capacitor, increasing the memory density per area. An increase in memory density, such as with a die shrink, typically equates to a reduced cost per bit of memory. Containers with large aspect ratios have been developed as DRAM microchips are reduced in size to fit more containers into the same area, or to fit the same number into a reduced area. Used in this application, the aspect ratio of a container is the ratio of the height to the diameter of the container. Thus, a container with a large aspect ratio is one with a large height relative to a diameter. Containers with large aspect ratios are typically more difficult to fabricate than containers with small aspect ratios. Further, a large aspect ratio may prevent the application of materials to, as well as the removal of debris from, the bottom of a container. DRAM microchips may benefit from the replacement of containers with a new technology.

U.S. Pat. No. 7,050,327, to Campbell (“the ’327 patent”), discloses a device, and the fabrication of the device, that may be used as a memory cell. The ’327 patent is incorporated herein, in its entirety, by reference. The device disclosed in the ’327 patent demonstrates DNR and has a variable electric current characteristic. For example, the electric current mea-

surable through the device when measured at a specific reading voltage, such as at 0.26V, can be changed by applying voltages within a certain range, such as within the range of 0.36V to 0.55V. The change in measurable electric current at the specific reading voltage is substantially persistent. Thus, a value can be stored in the device as a readable electric current value.

Changing a readable electric current value through a device diverges from the design of many types of DRAM, which generally use the aforementioned capacitive charge containers to store charge. Modern DRAM circuits use a measurement device, such as a sense amplifier, to measure the charge of a capacitive charge container. As such, non-capacitive memory devices may not be compatible with DRAM circuits, as they are currently designed.

The present disclosure is directed toward overcoming, or at least reducing the effects of one or more of the issues set forth above.

SUMMARY

A circuit is disclosed. The circuit may comprise a capacitive device. The capacitive device may comprise a first conductor, a chalcogenide layer, a metal chalcogenide layer, and a second conductor. The chalcogenide layer may be connected to the first conductor. The metal chalcogenide layer may be connected to the chalcogenide layer. The second conductor may be connected to the metal chalcogenide layer. The capacitive device may be configured to store charge.

The circuit may further comprise a source comprising a positive terminal and a negative terminal. The positive terminal may be connected to the first conductor and the negative terminal may be connected to the second conductor. Alternatively, the negative terminal may be connected to the first conductor and the positive terminal may be connected to the second conductor. The capacitive device may have a capacitance within the range of about 100 femtoFarads to about 100 picoFarads. The capacitive device may be configured to operate at a voltage of about 0.2 volts. The device may further comprise a metal layer. The metal layer may be disposed between the metal chalcogenide layer and the second conductor. The metal chalcogenide layer may be connected to the second conductor through the metal layer. The metal layer may comprise lead, tin, silver, indium, antimony, gold, or copper.

A memory circuit is disclosed. The memory circuit may comprise a capacitive device. The capacitive device may be connected to a sensing device. The capacitive device may comprise a first conductor, a chalcogenide layer, a metal chalcogenide layer, and a second conductor. The chalcogenide layer may be connected to the first conductor. The metal chalcogenide layer may be connected to the chalcogenide layer. The second conductor may be connected to the metal chalcogenide layer. The capacitive device may be configured to store a charge.

The sensing device may be configured to sense the charge stored in the capacitive device. The sensing device may comprise a sense amplifier. The first conductor may be connected to a voltage plane. The second conductor may be connected to a transistor. The second conductor may be connected to a voltage plane. The first conductor may be connected to a transistor.

A method is disclosed. The method may comprise providing a capacitive device. The capacitive device may comprise a metal chalcogenide layer, a first conductor, and a second conductor. The metal chalcogenide layer may be disposed between the first conductor and the second conductor. The

method may further comprise connecting the first conductor and the second conductor to a source. The method may further comprise applying a first voltage across the first and second conductors with the source. The method may further comprise storing charge from the applied voltage in the capacitive device. The charge may be substantially stored in the metal chalcogenide layer.

The method may further comprise removing the applied voltage from the first conductor and the second conductor after storing the charge. The method may further comprise measuring the stored charge at the first and second conductors after removing the applied voltage. The stored charge may be measured by a circuit comprising a sense amplifier. The method may further comprise releasing at least a portion of the stored charge from the device. The charge may be released if the first voltage applied across the first and second conductors is substantially reduced. The first voltage applied across the first conductor and the second conductor may be about 0.2 volts. The capacitive device may further comprise a metal layer. The metal layer may be connected to the metal chalcogenide layer. The method may further comprise setting the capacitance of the capacitive device by applying a second voltage to the capacitive device and migrating metal from the metal layer into the metal chalcogenide layer. The method may further comprise setting the capacitance of the capacitive device by applying a second voltage to the capacitive device and migrating metal from the metal chalcogenide layer into the metal layer.

These and other embodiments of the present application will be discussed more fully in the description. The features, functions, and advantages can be achieved independently in various embodiments of the claimed invention, or may be combined in yet other embodiments.

BRIEF DESCRIPTION OF FIGURES

FIG. 1 is a cutaway view of an embodiment of an integratable programmable capacitive device;

FIG. 2 is a close up view of a quantum dot doped metal chalcogenide layer;

FIG. 3 is a current-voltage graph showing the I-V curve of the embodiment of the integratable programmable capacitive device of FIG. 1;

FIG. 4 is a graph of capacitance versus frequency of the embodiment of the integratable programmable capacitive device of FIG. 1;

FIG. 5A is a partial view of a memory bank with an embodiment of an integratable programmable capacitive device;

FIG. 5B is a partial block diagram of a memory circuit;

FIG. 6 is a schematic of a circuit comprising an embodiment of an integratable programmable capacitive device.

Like reference numbers and designations in the various drawings indicate like elements.

DETAILED DESCRIPTION

In the following description, reference is made to the accompanying drawings that form a part thereof, and in which is shown by way of illustration specific exemplary embodiments in which the invention may be practiced. These embodiments are described in sufficient detail to enable those skilled in the art to practice the invention, and it is to be understood that modifications to the various disclosed embodiments may be made, and other embodiments may be utilized, without departing from the spirit and scope of the

present invention. The following detailed description is, therefore, not to be taken in a limiting sense.

The term “substrate” used in the following description may include any supporting structure including, but not limited to, a semiconductor substrate that has an exposed substrate surface. A semiconductor substrate should be understood to include silicon, epitaxial silicon, silicon-on-insulator (SOI), silicon-on-sapphire (SOS), doped and undoped semiconductors, epitaxial layers of silicon supported by a base semiconductor foundation, and other semiconductor structures. When reference is made to a substrate in the following description, previous process steps may have been utilized to form regions or junctions in or over the base substrate or foundation. The substrate need not be semiconductor-based, but may be any support structure suitable for supporting the disclosed device, including, but not limited to, metals, alloys, glasses, natural and synthetic polymers, ceramics, fabrics, and any other suitable materials, as would be apparent to one of ordinary skill in the art, given the benefit of this disclosure.

FIG. 1 is a cross-sectional view of an embodiment of an integratable programmable capacitive device **100**, such as might be fabricated on a semiconductor wafer. The integratable programmable capacitive device **100** comprises a substrate **102**, a first insulative layer **104**, a first conductor **106**, a chalcogenide layer **108**, a metal chalcogenide layer **110**, a metal layer **112**, an adhesive layer **114**, a second conductor **116**, and a second insulative layer **118**. One or more of the layers may be optional. For example, the adhesion layer **114** may not be needed to adhere the conductor **116** to the metal layer **112**. Also, additional layers may be added in between one or more of the layers. For example, additional adhesion layers may be added between one or more layers.

The first insulative layer **104** may be fabricated over the substrate **102**, which acts to support the integratable programmable capacitive device **100**. The first insulative layer **104** may comprise one or more materials, such as an oxide material, a nitride material, or another suitable insulative material, as would be apparent to one of ordinary skill in the art, given the benefit of this disclosure. The first insulative layer **104** may be fabricated on the substrate **102** through any method known in the art. Alternatively, the integratable programmable capacitive device **100** may be fabricated directly on the substrate **102**.

The first conductor **106** may be fabricated on the first insulative layer **104**. The first conductor **106** may be copper, aluminum, tungsten, or another suitable conductive material, as would be apparent to one of ordinary skill in the art, given the benefit of this disclosure. The first conductor **106** may connect to further conductive layers or circuitry, such as a voltage plane, a ground plane, a voltage supply, a driver circuit, a difference amplifier, a sense amplifier, or to other suitable circuitry, as would be apparent to one of ordinary skill in the art, given the benefit of this disclosure.

Chalcogens are generally represented on the periodic table of elements in Group 16, which comprises, among other elements, sulfur (S), selenium (Se), and tellurium (Te). A chalcogenide is generally a compound with an element from the chalcogen group and an electropositive element, such as, for example, cadmium (Cd), germanium (Ge), lead (Pb), tin (Sn), or copper (Cu). A metal chalcogenide is a generally a compound with an element from the chalcogen group and a metal, such as, for example, lead (Pb), tin (Sn), silver (Ag), indium (In), antimony (Sb), gold (Au), copper (Cu), or another suitable metal.

The chalcogenide layer **108** is fabricated on the first conductor layer **106** and may have a height of about 300 angstroms. Alternatively, the height of the chalcogenide layer

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108 may be another suitable height. The chalcogenide layer **108** may comprise $\text{Ge}_x\text{Se}_{(100-x)}$, where x may be in the range of about 18 to about 40, such as 20, 25, or 40. For example, the chalcogenide layer **108** may comprise $\text{Ge}_{40}\text{Se}_{60}$, which also may be expressed as Ge_2Se_3 . Alternatively, the chalcogenide layer **108** may comprise, for example, cadmium and tellurium, which may form cadmium telluride (CdTe), or other suitable elements.

The metal chalcogenide layer **110** is fabricated on the chalcogenide layer **108** and may have a height of about 500 angstroms. Alternatively, the height of the metal chalcogenide layer **110** may be another suitable height. The metal chalcogenide layer **110** may comprise materials such as PbSe , SnSe , In_2Se_3 , Ag_2Se , Sb_2Se_3 , Cu_2Se , or other suitable materials.

The metal layer **112** may be fabricated over the metal chalcogenide layer **110** and may have a height of about 150 angstroms. Alternatively, the height of the metal layer **112** may be another suitable height. The metal layer **112** may comprise silver, copper, or another suitable metal.

The second conductor **116** may be fabricated directly on the metal layer **112**. Alternatively, the second conductor **116** may connect to the metal layer **112** through an adhesive layer **114** that may aid in the connection of dissimilar materials. The adhesive layer may comprise, for example, a Metal-doped Ge_2Se_3 layer, such as Ag-doped Ge_2Se_3 , Cu-doped Ge_2Se_3 , or another suitable material. The second conductor **116** may comprise the same material as the first conductor **106**, the same material as the metal layer **112**, or may comprise, for example, copper, silver, aluminum, tungsten, or another suitable conductive material.

The second conductor **116** may connect to further conductive layers or circuitry, such as a voltage plane, a ground plane, a voltage supply, a driver circuit, a difference amplifier, a sense amplifier, or to other suitable circuitry, and may correspond with or complement conductive layers or circuitry that the first conductor **106** may be connected with.

An insulative fill layer **118** is also shown in FIG. 1, which may fill the spaces that are above and/or to the sides of the layers **106** through **116** of the integratable programmable capacitive device **100**. The insulative layer **118** may encapsulate the integratable programmable capacitive device **100**. The fill layer **118** may act to physically support the integratable programmable capacitive device **100** and may further act to isolate the layers. For example, the fill layer **118** may act to reduce effects from electric and/or magnetic fields that may be produced from or near the integratable programmable capacitive device **100**.

After the layers of the integratable programmable capacitive device **100** have been fabricated, a capacitance characteristic of the integratable programmable capacitive device **100** may be programmed. For an integratable programmable capacitive device **100** of about 0.25 micrometers in diameter in contact with the bottom electrode and with active material under the top electrode having an area of about 80 micrometers by about 80 micrometers, the capacitance may be programmed to be within a range from about 20 femtoFarads to about 100 picoFarads. To program the capacitance, a voltage may be applied across the first and second conductors **106**, **116**. The voltage may be a short pulse and may influence molecules from the metal layer **112** to move into the metal chalcogenide layer **110**.

For example, if the metal layer **112** comprises silver, silver molecules may migrate from the metal layer **112** into the metal chalcogenide layer **110** upon application of the voltage. Characteristics of the voltage, such as, the magnitude and/or the rise time may determine the amount of silver that migrates

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into the metal chalcogenide layer **110**. For larger programmed capacitances, a larger amount of the silver should be migrated into the metal chalcogenide layer **110**.

Some or all of the metal of the metal layer **112** may be integrated into the metal chalcogenide layer **110** at the time of fabrication of the layer through, for example, by a sputtering process, photo diffusion, thermal diffusion, or another suitable process. Thus, in some embodiments, the metal layer **112** may be reduced in height or omitted.

FIG. 2 is a close up, cut away view of a portion of the integratable programmable capacitive device **100** of FIG. 1, after the capacitance characteristic has been programmed. As shown in FIG. 2, when metal from the metal layer **112** is migrated into the metal chalcogenide layer **110**, small nodules of the metal, quantum dots **120**, are formed throughout the metal chalcogenide layer **110**. The metal chalcogenide layer **110** is effectively doped with quantum dots **120**.

Typically, quantum dots **120** resonate within a set range of frequencies at a set range of voltages. Electrons may move or “tunnel” from one quantum dot **120** to another quantum dot **120** when conditions are favorable. This phenomenon is referred to as quantum tunneling or the tunnel effect. Generally, more favorable conditions lead to more electrons moving through the material.

The flow of electrons enabled by tunneling may be controlled. Electron mobility through the quantum dot doped metal chalcogenide layer **110** may be high or may be substantially stopped, depending on the voltage across the first and second conductors **106**, **116**. For example, if a tunneling flow of electrons is started and then stopped within suitable parameters, the quantum dots **120** will each continue to hold a measurable charge. Because the tunneling behavior has been inhibited, the charge remaining on the quantum dots **120** has no path through which to discharge, and will thus remain in the integratable programmable capacitive device **100** for a substantial amount of time. For example, the integratable programmable capacitive device **100** may hold a charge for long enough to be used as a semi-non-volatile memory device, with a long refresh time, such as a refresh time that is about one second. In another example, the integratable programmable capacitive device **100** may hold a charge for long enough to be considered a non-volatile memory device. By contrast, modern DRAM has a refresh rate of about 0.066 seconds or 66 milliseconds, meaning that each memory bit must be refreshed every 66 milliseconds.

Control of the tunneling behavior allows the integratable programmable capacitive device **100** to act like a capacitor. When quantum dots **120** hold charge, the integratable programmable capacitive device **100** appears as a charged capacitor. Alternatively, a voltage may be applied across the first and second conductors **106**, **116** to discharge the quantum dots **120**, making the integratable programmable capacitive device **100** appear as a discharged capacitor. Further, the integratable programmable capacitive device **100** may be charged and discharged in a manner similar to many known capacitors. For example, charge may be stored in and/or released from the integratable programmable capacitive device **100** in a controlled and predictable way.

When the capacitance of the integratable programmable capacitive device **100** has been set (i.e., metal has been suitably introduced into the metal-chalcogenide layer **110**), the integratable programmable capacitive device **100** exhibits a DNR characteristic as well as an increased capacitance.

FIG. 3 shows an electric current (I) (labeled as “A” for Amperes or Amps, on FIG. 1) versus voltage (V) graph illustrating a typical I-V curve of an embodiment of the integratable programmable capacitive device **100**. The I-V curve

illustrates the DNR characteristic of the integratable programmable capacitive device **100**. Moving from zero to positive voltage, the current increases until the voltage reaches about 0.2 volts, where the current peaks. Near this peak, an increase in voltage does not result in an increase in current. In fact, as the voltage increases beyond the peak, the current begins to drop, illustrating the start of a DNR region. Thereafter, the I-V curve may show a voltage minimum or trough (not shown) such that as the voltage increases past the voltage minimum, the current may again begin to increase, illustrating the end of the DNR region.

FIG. **4** shows a graph that illustrates a capacitance characteristic of an embodiment of the integratable programmable capacitive device **100** over a range of frequencies on a logarithmic scale. The integratable programmable capacitive device **100** that was measured to generate the data used to create the graph shown in FIG. **4** has a diameter of about 0.25 micrometer (250 nanometers) and a height of about 150 nanometers. By contrast, a typical charge container used in modern DRAM circuits may be about 90 nanometers in diameter and have a height of about 1 micrometer (1,000 nanometers). As illustrated in FIG. **4**, the frequency response of the tested integratable programmable capacitive device **100** is shown at three test voltages (0.2V, 0.5V, and 2.0V) and across a range of frequencies (from about 1 kilohertz (KHz) to about 100 KHz).

As seen in FIG. **4**, the graph lines illustrating operation at 0.2V and 0.5V indicate a much higher capacitance than the graph line illustrating operation at 2.0V. The graph line illustrating operation at 0.2V shows a capacitance that is comparable with the capacitance of the 0.5V graph line at lower frequencies. At higher frequencies, the graph line illustrating operation at 0.2V shows a much greater capacitance than the 0.5V graph line. The line illustrating 2.0V may indicate a breakdown in the device. A device breakdown may indicate, for example, metal migration due to the increased voltage, breaking down the tunnel effect.

As can be seen in FIG. **4**, the tested integratable programmable capacitive device **100** has a capacitance in the range of 0.1 nanoFarads (10-10 F) at about 3 KHz and at 0.2V operating voltage. By contrast, capacitive charge containers used in modern DRAM circuits operate at a capacitance measuring in the femtoFarad range (10-15 F). Thus, the integratable programmable capacitive device **100** of the current disclosure may have a capacitance that is many orders of magnitude larger than currently used capacitive devices, with a lateral cross-sectional area that may be considered substantially similar to the diameter of currently used capacitive devices, or at least less than one order of magnitude different. Additionally, the device currently disclosed may be only about 150 nanometers in height, rather than the about 1,000 nanometers of current charge containers. This may allow for a shortened time of fabrication and may advantageously allow stacking of charge containers comprising embodiments of the integratable programmable capacitive device **100**.

FIG. **5A** illustrates a partial schematic of a memory bank **500** for a DRAM circuit. As shown in FIG. **5A**, a memory bit (memory bit) **510** comprising an integratable programmable capacitive device **515** may have a substantially similar design as current DRAM, with one transistor **505** and one capacitive device **515** per memory bit **510**. Additionally, because the memory bits **510** have a small aspect ratio, relative to previous capacitive charge containers, banks of memory bits may be fabricated in layers. For example, a first memory bit layer may be fabricated over a second memory bit layer. Additional layers, such as insulative layers and/or isolation layers, may be fabricated between the first and second memory bit layers.

FIG. **5B** is a partial block diagram of an embodiment of a memory circuit, such as DRAM. As illustrated by FIG. **5B**, the memory bank **500** may be connected to a sensing device bank **520**. Each memory bit **510** may be connected to one or more sensing devices within the sensing device bank **520**. The sensing device bank **520** may comprise one or more sensing devices, such as, for example, differential amplifiers, sense amplifiers, capacitance sensing devices, voltage sensing devices, current sensing devices, charge sensing devices, or other suitable sensing devices.

Embodiments of the integratable programmable capacitive device **100** may also be employed as capacitive devices in other areas of a microchip or electronic device. For example, the integratable programmable capacitive device **100** may be fabricated near fast switching devices or other devices that demand power intermittently, to store and release charge. For example, a voltage may be applied to the integratable programmable capacitive device **100**, and the integratable programmable capacitive device may store charge from the applied voltage. The charge stored by the integratable programmable capacitive device **100** may then be available to nearby connected conductors and/or devices if the applied voltage dips or changes substantially. As such, the integratable programmable capacitive device **100** may act as an on-die decoupling capacitor, a bypass capacitor, a power capacitor, and/or a bulk capacitor. Additionally, the integratable programmable capacitive device **100** may be used in place of capacitors used in conventional circuits.

FIG. **6** shows a schematic of a circuit **610** with voltage and ground connections **602**, **604**. An embodiment of the integratable programmable capacitive device **600** is coupled between the voltage and ground connections to supply charge to the circuit **610** in the case that a connected source **615** cannot supply adequate current to the circuit **610** at peak usage.

Other applications for an embodiment of an integratable programmable capacitive device, such as a replacement for a bypass capacitor or for another capacitive device well known in the art, would be apparent to one of ordinary skill in the art, given the benefit of this disclosure.

Although this invention has been described in terms of certain preferred embodiments, other embodiments that are apparent to those of ordinary skill in the art, including embodiments that do not provide all of the features and advantages set forth herein, are also within the scope of this invention. Therefore, the scope of the present invention is defined only by reference to the appended claims and equivalents thereof.

What is claimed is:

1. A circuit comprising:

a capacitive device, the capacitive device comprising:

a first conductor;

a chalcogenide layer connected to the first conductor;

a metal chalcogenide layer connected to the chalcogenide layer; and

a second conductor connected to the metal chalcogenide layer,

wherein the capacitive device is configured to store charge.

2. The circuit of claim 1, further comprising a source, the source having a positive terminal connected to the first conductor and a negative terminal connected to the second conductor.

3. The circuit of claim 1, further comprising a source, the source having a positive terminal connected to the second conductor and a negative terminal connected to the first conductor.

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4. The circuit of claim 1, wherein the capacitive device has a capacitance between the range of about 100 femtoFarads to about 100 picoFarads.

5. The circuit of claim 1, wherein the capacitive device is configured to operate at a voltage of about 0.2 volts.

6. The circuit of claim 1, wherein the device further comprises a metal layer disposed between the metal chalcogenide layer and the second conductor, the metal chalcogenide layer being connected to the second conductor through the metal layer.

7. The circuit of claim 6, wherein the metal layer comprises lead, tin, silver, indium, antimony, gold, or copper.

8. A memory circuit comprising:
a capacitive device connected to a sensing device,
the capacitive device comprising
a first conductor;
a chalcogenide layer connected to the first conductor;
a metal chalcogenide layer connected to the chalcogenide layer; and
a second conductor connected to the metal chalcogenide layer;
wherein the capacitive device is configured to store a charge.

9. The memory circuit of claim 8, wherein the sensing device is configured to sense the charge stored in the capacitive device.

10. The memory circuit of claim 8, wherein the sensing device comprises a sense amplifier.

11. The memory circuit of claim 8, wherein the first conductor is connected to a voltage plane and the second conductor is connected to a transistor.

12. The memory circuit of claim 8, wherein the second conductor is connected to a voltage plane and the first conductor is connected to a transistor.

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13. A method comprising:
providing a capacitive device comprising a metal chalcogenide layer disposed between a first conductor and a second conductor;
connecting the first conductor and the second conductor to a source;
applying a first voltage across the first and second conductors with the source;
storing charge from the applied voltage in the capacitive device,
wherein the charge is substantially stored in the metal chalcogenide layer.

14. The method of claim 13, further comprising removing the applied voltage from the first conductor and the second conductor after storing the charge.

15. The method of claim 14, further comprising measuring the stored charge at the first and second conductors after removing the applied voltage.

16. The method of claim 15, wherein the stored charge is measured by a circuit comprising a sense amplifier.

17. The method of claim 13, further comprising releasing at least a portion of the stored charge from the device if the first voltage applied across the first and second conductors is substantially reduced.

18. The method of claim 13, wherein the capacitive device further comprises a metal layer connected to the metal chalcogenide layer.

19. The method of claim 18, further comprising setting the capacitance of the capacitive device by applying a second voltage to the capacitive device and migrating metal from the metal layer into the metal chalcogenide layer.

20. The method of claim 18, further comprising setting the capacitance of the capacitive device by applying a second voltage to the capacitive device and migrating metal from the metal chalcogenide layer into the metal layer.

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